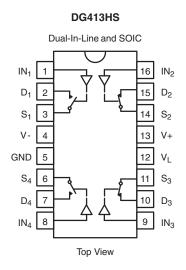
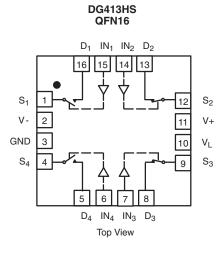
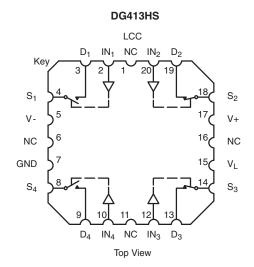


FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION







TRUTH TABLE									
Logic	SW ₁ , SW ₄	SW ₂ , SW ₃							
0	OFF	ON							
1	ON	OFF							

Temp. Range	Package	Part Number
DG411HS, DG412HS		
		DG411HSDJ
	16-Pin Plastic DIP	DG411HSDJ-E3
	10-FIII Flastic DIF	DG412HSDJ
		DG412HSDJ-E3
		DG411HSDY
		DG411HSDY-E3
40 °C to 05 °C		DG411HSDY-T1
- 40 °C to 85 °C	16-Pin Narrow SOIC	DG411HSDY-T1-E3
	10-Fill Nation SOIC	DG412HSDY
		DG412HSDY-E3
		DG412HSDY-T1
		DG412HSDY-T1-E3
	16 Din OFN 4 v 4 mm (Variation 1)	DG411HSDN-T1-E4
	16-Pin QFN 4 x 4 mm (Variation 1)	DG412HSDN-T1-E4
DG413HS		
	16-Pin Plastic DIP	DG413HSDJ
	16-FIII Flastic DIF	DG413HSDJ-E3
		DG413HSDY
- 40 °C to 85 °C	16-Pin Narrow SOIC	DG413HSDY-E3
	10-FIII NAITOW SOIC	DG413HSDY-T1
		DG413HSDY-T1-E3
	16-Pin QFN 4 x 4 mm (Variation 1)	DG413HSDN-T1-E4





ABSOLUTE MAXIMUM RATINGS								
Parameter		Limit	Unit					
V+ to V-		44						
GND to V-		25						
V _L		(GND - 0.3) to (V+) + 0.3	V					
Digital Inputs ^a , V _S , V _D		(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first						
Continuous Current (Any terminal)		30	mA					
Peak Current, S or D (Pulsed 1 ms, 10 %	6 duty cycle)	100	IIIA					
Storage Temperature	(AK, AZ Suffix)	- 65 to 150	°C					
Storage remperature	(DJ, DY, DN Suffix)	- 65 to 125						
	16-Pin Plastic DIP ^c	470						
	16-Pin Narrow SOIC ^d	600						
Power Dissipation (Package) ^b	16-Pin CerDIP ^e	900	mW					
	LCC-20 ^e	900	7					
	16-Pin (4 x 4 mm) QFN ^f	1880						

- $a. \ Signals \ on \ S_X, \ D_X, \ or \ IN_X \ exceeding \ V+ \ or \ V- \ will \ be \ clamped \ by \ internal \ diodes. \ Limit \ forward \ diode \ current \ to \ maximum \ current \ ratings.$
- b. All leads welded or soldered to PC board.
- c. Derate 6 mW/°C above 25 °C.
- d. Derate 7.6 mW/°C above 75 °C.
- e. Derate 12 mW/°C above 75 °C.
- f. Derate 23.5 mW/°C above 70 °C.

SPECIFICATIONS ^a										
		Test Conditions Unless Specified			A Suffix - 55 °C to 125 °C		D Suffix - 40 °C to 85 °C			
Parameter	Symbol	V+ = 15 V, V- = -15 V $V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^f$	Temp.b	Typ. ^c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	Unit	
Analog Switch									•	
Analog Signal Range ^e	V _{ANALOG}		Full		- 15	15	- 15	15	V	
Drain-Source On-Resistance	R _{DS(on)}	V+ = 13.5 V, V- = -13.5 V $I_S = -10 \text{ mA}, V_D = \pm 8.5 \text{ V}$	Room Full	25		35 45		35 45	Ω	
Switch Off	I _{S(off)}	V+ = 16.5 V, V- = - 16.5 V	Room Full	± 0.1	- 0.25 - 20	0.25 20	- 0.25 - 5	0.25 5		
Leakage Current	I _{D(off)}	$V_D = \pm 15.5 \text{ mA}, V_S = \pm 15.5 \text{ V}$	Room Full	± 0.1	- 0.25 - 20	0.25 20	- 0.25 - 5	0.25 5	nA	
Channel On	,	V+ = 16.5 V, V- = - 16.5 V Room ± 0.1		± 0.1	- 0.4	0.4	- 0.4	0.4		
Leakage Current	I _{D(on)}	$V_D = V_S = \pm 15.5 \text{ V}$	Full		- 40	40	- 10	10		
Digital Control										
Input Current, V _{IN} Low	Ι _Ι	V _{IN} under test = 0.8 V	Full	0.005	- 0.5	0.5	- 0.5	0.5	μΑ	
Input Current, V _{IN} High	I _{IH}	V _{IN} under test = 2.4 V	Full	0.005	- 0.5	0.5	- 0.5	0.5	μΑ	
Input Capacitance ^e	C _{IN}	f = 1 MHz	Room	5					pF	
Dynamic Characteristics										
Turn-On Time	t _{ON}	$R_L = 300 \Omega$, $C_L = 35 pF$	Room Full	68		105 127		105 116		
Turn-Off Time	t _{OFF}	$V_S = \pm 10 \text{ V}$, see figure 2	Room Full	42		80 94		80 90	ns	
Break-Before-Make Time Delay	t _D	DG413HS only, $V_S = 10 \text{ V}$ $R_L = 300 \Omega$, $C_L = 35 \text{ pF}$	Room	20						
Charge Injection ^e	Q	$V_{g} = 0 \text{ V}, R_{g} = 0 \Omega, C_{L} = 10 \text{ nF}$	Room	22					рС	

DG411HS, DG412HS, DG413HS

Vishay Siliconix



SPECIFICATIONS ^a										
	Test Conditions Unless Specified				A Suffix - 55 °C to 125 °C		D Suffix - 40 °C to 85 °C			
Parameter	Symbol	V+ = 15 V, V- = -15 V $V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^f$	Temp.b	Typ. ^c	Min.d	Max. ^d	Min. ^d	Max. ^d	Unit	
Dynamic Characteristics (Conf	.'d)									
Off Isolation ^e	OIRR	$R_L = 50 \Omega, C_L = 5 pF$	Room	- 91					dB	
Channel-to-Channel Crosstalke	X _{TALK}	f = 1 MHz	Room	- 88					aв	
Source Off Capacitance ^e	C _{S(off)}		Room	12						
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz	Room	12					pF	
Channel On Capacitance ^e	C _{D(on)}		Room	30						
Power Supplies										
Positive Supply Current	l+		Room Full	0.0001		1 5		1 5		
Negative Supply Current	 -	V+ = 16.5 V, V- = - 16.5 V	Room Full	- 0.0001	- 1 - 5		- 1 - 5			
Logic Supply Current	ΙL	$V_{IN} = 0$ or 5 V	Room Full	0.0001		1 5		1 5	μΑ	
Ground Current	I _{GND}		Room Full	- 0.0001	- 1 - 5		- 1 - 5			

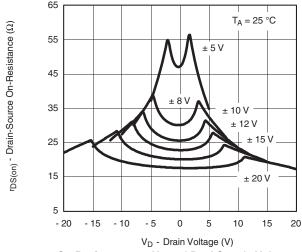
SPECIFICATIONS ^a (fo	SPECIFICATIONS ^a (for Unipolar Supplies)										
		Test Conditions Unless Specified			_	uffix o 125°C	D Suffix - 40 °C to 85 °C				
Parameter	Symbol	$V_{+} = 12 \text{ V}, V_{-} = 0 \text{ V}$ $V_{L} = 5 \text{ V}, V_{IN} = 2.4 \text{ V}, 0.8 \text{ V}^{f}$	Temp.b	Typ. ^c	Min.d	Max. ^d	Min.d	Max. ^d	Unit		
Analog Switch	_				L	L	L	L			
Analog Signal Range ^e	V _{ANALOG}		Full			12		12	V		
Drain-Source On-Resistance	R _{DS(on)}	$V+ = 10.8 \text{ V}, I_S = -10 \text{ mA}$ $V_D = 3 \text{ V}, 8 \text{ V}$	Room Full	49		80 100		80 100	Ω		
Dynamic Characteristics											
Turn-On Time	t _{ON}	$R_1 = 300 \Omega, C_1 = 35 pF$	Room Hot	95		140 180		140 160			
Turn-Off Time	t _{OFF}	$V_S = 8 \text{ V}$, see figure 2	Room Hot	36		70 79		70 74	ns		
Break-Before-Make Time Delay	t _D	DG413HS only, $V_S = 8 \text{ V}$ $R_L = 300 \Omega$, $C_L = 35 \text{ pF}$	Room	60							
Charge Injection	Q	$V_g = 6 \text{ V}, R_g = 0 \Omega, C_L = 1 \text{ nF}$	Room	60					рC		
Power Supplies											
Positive Supply Current	I+		Room Hot	0.0001		1 5		1 5			
Negative Supply Current	l-	V: 100VV 0 - 5V	Room Hot	- 0.0001	- 1 - 5		- 1 - 5				
Logic Supply Current	ΙL	V+ = 13.2 V, V _{IN} = 0 or 5 V	Room Hot	0.0001		1 5		1 5	μΑ		
Ground Current	I _{GND}		Room Hot	- 0.0001	- 1 - 5		- 1 - 5				

- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25 $^{\circ}$ C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.

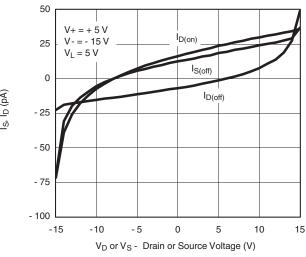
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



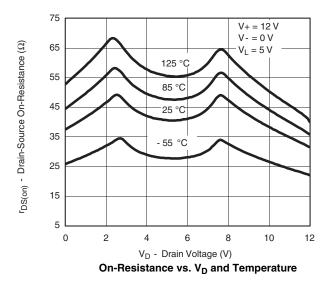
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. $V_{\rm D}$ and Dual Supply Voltage

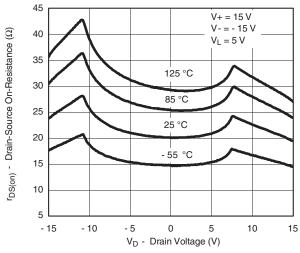


Leakage Current vs. Analog Voltage

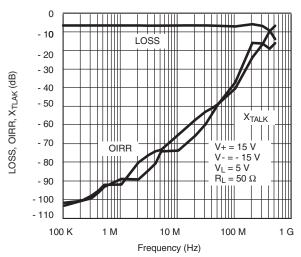


300 T_A = 25 °C ${}^{r}{}_{DS(on)}$ - Drain-Source On-Resistance (Ω) $V_L = 5 V$ V + = 3.0 V250 $V_L = 3 V$ 200 V + = 5.0 V150 100 V+ = 15.0 V 50 V + = 20.0 V0 16 V_D - Drain Voltage (V)

On-Resistance vs. V_D and Unipolar Supply Voltage



On-Resistance vs. V_D and Temperature

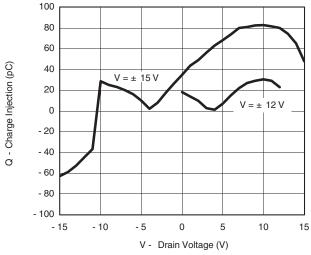


Insertion Loss, Off-Isolation, Crosstalk vs. Frequency

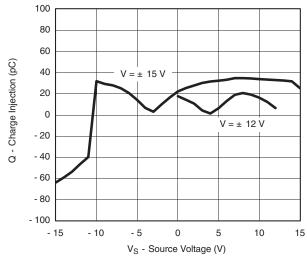
DG411HS, DG412HS, DG413HS

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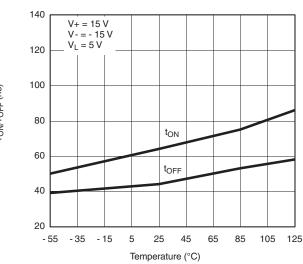
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



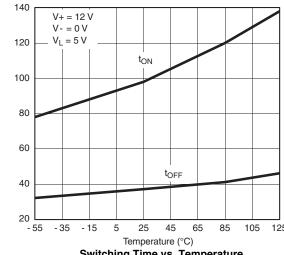
Charge Injection vs. Analog Voltage



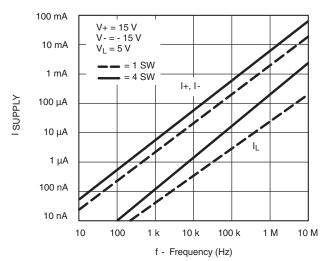
Charge Injection vs. Analog Voltage



Switching Time vs. Temperature



Switching Time vs. Temperature



Supply Current vs. Input Switching Frequency

TON TOFF (ns)



SCHEMATIC DIAGRAM (Typical Channel)

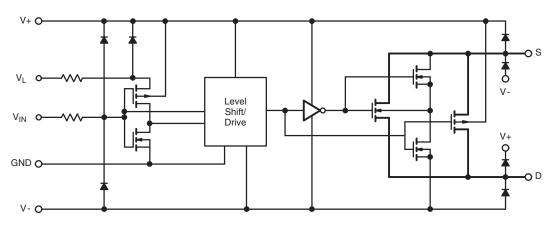
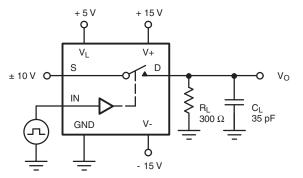
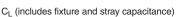


Figure 1.

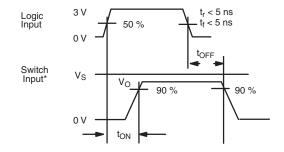
TEST CIRCUITS





$$V_O = V_S$$

$$\frac{R_L}{R_L + r_{DS(on)}}$$



Note: Logic input waveform is inverted for switches that have the opposite logic sense control

Figure 2. Switching Time

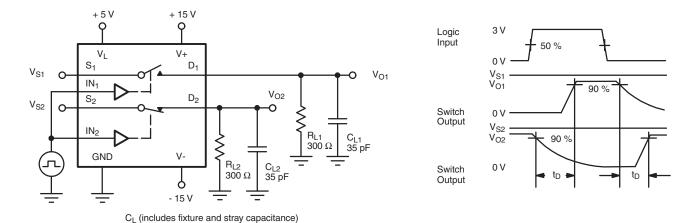


Figure 3. Break-Before-Make (DG413HS)

TEST CIRCUITS



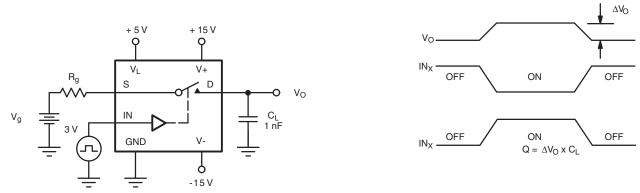


Figure 4. Charge Injection

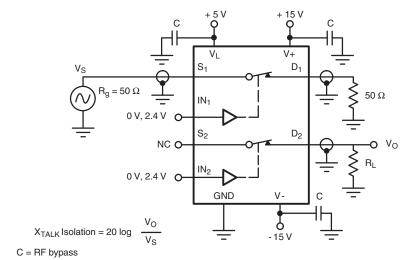
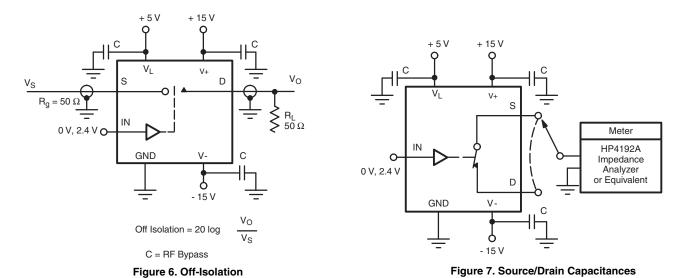


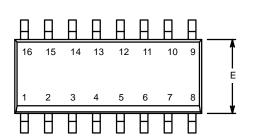
Figure 5. Crosstalk



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72053.



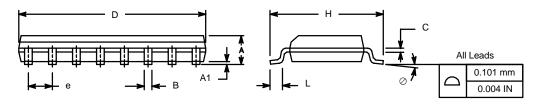
SOIC (NARROW): 16-LEAD
JEDEC Part Number: MS-012



	MILLIM	ILLIMETERS INCHES		
Dim	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
В	0.38	0.51	0.015	0.020
С	0.18	0.23	0.007	0.009
D	9.80	10.00	0.385	0.393
E	3.80	4.00	0.149	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
L	0.50	0.93	0.020	0.037
0	0°	8°	0°	8°
FCN: S-0	3946—Rev F	09 lul-01		

ECN: S-03946—Rev. F, 09-Jul-01

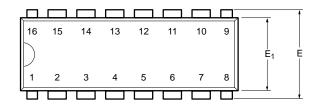
DWG: 5300

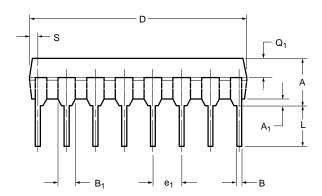


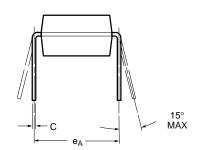
Document Number: 71194 www.vishay.com 02-Jul-01 sww.vishay.com



PDIP: 16-LEAD



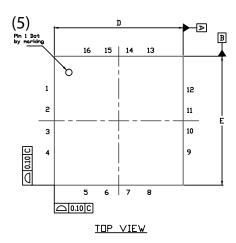


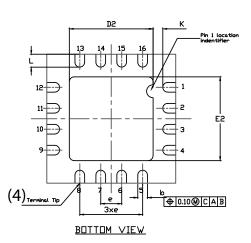


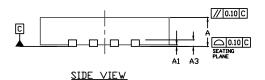
	MILLIM	IETERS	INC	HES				
Dim	Min	Max	Min	Max				
Α	3.81	5.08	0.150	0.200				
A ₁	0.38	1.27	0.015	0.050				
В	0.38	0.51	0.015	0.020				
B ₁	0.89	1.65	0.035	0.065				
С	0.20	0.30	0.008	0.012				
D	18.93	21.33	0.745	0.840				
Е	7.62	8.26	0.300	0.325				
E ₁	5.59	7.11	0.220	0.280				
e ₁	2.29	2.79	0.090	0.110				
e _A	7.37	7.87	0.290	0.310				
L	2.79	3.81	0.110	0.150				
Q_1	1.27	2.03	0.050	0.080				
S	0.38	1.52	.015	0.060				
ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5482								

Document Number: 71261 www.vishay.com 06-Jul-01 sum.vishay.com

QFN 4x4-16L Case Outline







	VARIATION 1					VARIATION 2						
DIM	МІ	MILLIMETERS ⁽¹⁾		INCHES		MILLIMETERS ⁽¹⁾		S ⁽¹⁾		INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	0.75	0.85	0.95	0.029	0.033	0.037	0.75	0.85	0.95	0.029	0.033	0.037
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
A3	0.20 ref.			0.008 ref.		0.20 ref.				0.008 ref.		
b	0.25	0.30	0.35	0.010	0.012	0.014	0.25	0.30	0.35	0.010	0.012	0.014
D		4.00 BS0)		0.157 BSC		4.00 BSC 0.157		0.157 BSC	BSC		
D2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106
е		0.65 BS0			0.026 BSC		0.65 BSC				0.026 BSC	
Е		4.00 BS0			0.157 BSC		4.00 BSC			0.157 BSC		
E2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106
K		0.20 min			0.008 min.			0.20 min.		0.008 min.		
L	0.5	0.6	0.7	0.020	0.024	0.028	0.3	0.4	0.5	0.012	0.016	0.020
N ⁽³⁾		16		16		16			16			
Nd ⁽³⁾		4			4 4				4			
Ne ⁽³⁾		4			4			4			4	

Notes

- (1) Use millimeters as the primary measurement.
- (2) Dimensioning and tolerances conform to ASME Y14.5M. 1994.
- (3) N is the number of terminals. Nd and Ne is the number of terminals in each D and E site respectively.
- (4) Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.
- (5) The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.
- (6) Package warpage max. 0.05 mm.

ECN: S13-0893-Rev. B, 22-Apr-13

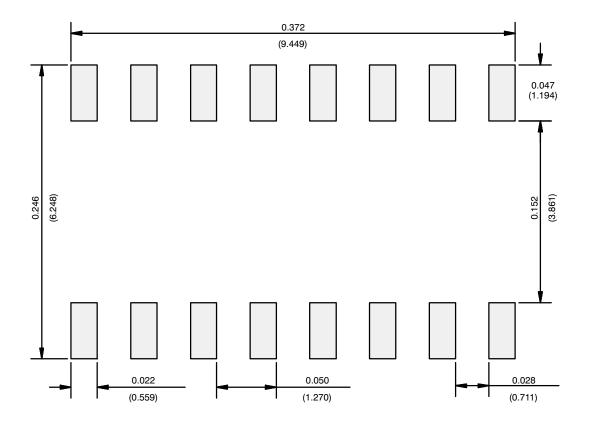
DWG: 5890

Revision: 22-Apr-13

Document Number: 71921



RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE

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